

Seongil Im

List of Publications by Year in descending order

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81743

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all docs

150
docs citations

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times ranked

8963
citing authors

#	ARTICLE	IF	CITATIONS
1	MoS ₂ Nanosheet Phototransistors with Thickness-Modulated Optical Energy Gap. Nano Letters, 2012, 12, 3695-3700.	4.5	1,221
2	Transparent and Photo-stable ZnO Thin-film Transistors to Drive an Active Matrix Organic-Light-Emitting-Diode Display Panel. Advanced Materials, 2009, 21, 678-682.	11.1	383
3	Ultraviolet-enhanced photodiode employing n-ZnO/p-Si structure. Applied Physics Letters, 2003, 83, 2946-2948.	1.5	368
4	Electric and Photovoltaic Behavior of a Few-Layer \pm -MoTe ₂ /MoS ₂ Dichalcogenide Heterojunction. Advanced Materials, 2016, 28, 3216-3222.	11.1	236
5	MoS ₂ Nanosheets for Top-Gate Nonvolatile Memory Transistor Channel. Small, 2012, 8, 3111-3115.	5.2	219
6	Photodetecting properties of ZnO-based thin-film transistors. Applied Physics Letters, 2003, 83, 5313-5315.	1.5	170
7	Black Phosphorus-Zinc Oxide Nanomaterial Heterojunction for p-n Diode and Junction Field-Effect Transistor. Nano Letters, 2016, 16, 1293-1298.	4.5	141
8	Nonvolatile Ferroelectric Memory Circuit Using Black Phosphorus Nanosheet-Based Field-Effect Transistors with P(VDF-TrFE) Polymer. ACS Nano, 2015, 9, 10394-10401.	7.3	130
9	Ultrasensitive PbS quantum-dot-sensitized InGaZnO hybrid photoinverter for near-infrared detection and imaging with high photogain. NPG Asia Materials, 2016, 8, e233-e233.	3.8	129
10	Homogeneous 2D MoTe ₂ p-n Junctions and CMOS Inverters formed by Atomic-Layer-Deposition-Induced Doping. Advanced Materials, 2017, 29, 1701798.	11.1	117
11	Low Power Consumption Complementary Inverters with n-MoS ₂ and p-WSe ₂ Dichalcogenide Nanosheets on Glass for Logic and Light-Emitting Diode Circuits. ACS Applied Materials & Interfaces, 2015, 7, 22333-22340.	4.0	113
12	Correlation between photoelectric and optical absorption spectra of thermally evaporated pentacene films. Applied Physics Letters, 2004, 84, 1701-1703.	1.5	109
13	Static and Dynamic Performance of Complementary Inverters Based on Nanosheet \pm -MoTe ₂ p-Channel and MoS ₂ n-Channel Transistors. ACS Nano, 2016, 10, 1118-1125.	7.3	98
14	Mixed-Dimensional 1D ZnO-2D WSe ₂ van der Waals Heterojunction Device for Photosensors. Advanced Functional Materials, 2017, 27, 1703822.	7.8	98
15	Pentacene thin-film transistors with Al ₂ O _{3+x} gate dielectric films deposited on indium-tin-oxide glass. Applied Physics Letters, 2003, 83, 2689-2691.	1.5	94
16	Vertical and In-Plane Current Devices Using NbS ₂ /n-MoS ₂ van der Waals Schottky Junction and Graphene Contact. Nano Letters, 2018, 18, 1937-1945.	4.5	86
17	Dual Gate Black Phosphorus Field Effect Transistors on Glass for NOR Logic and Organic Light Emitting Diode Switching. Nano Letters, 2015, 15, 5778-5783.	4.5	83
18	Metal Semiconductor Field-Effect Transistor with MoS ₂ /Conducting NiO van der Waals Schottky Interface for Intrinsic High Mobility and Photoswitching Speed. ACS Nano, 2015, 9, 8312-8320.	7.3	82

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19	Enhanced device performances of WSe ₂ /MoS ₂ van der Waals junction p-n diode by fluoropolymer encapsulation. Journal of Materials Chemistry C, 2015, 3, 2751-2758.	2.7	74
20	Self-Limiting Layer Synthesis of Transition Metal Dichalcogenides. Scientific Reports, 2016, 6, 18754.	1.6	74
21	High-Performance, Air-Stable, Top-Gate, p-Channel WSe ₂ Field-Effect Transistor with Fluoropolymer Buffer Layer. Advanced Functional Materials, 2015, 25, 7208-7214.	7.8	67
22	ZnO composite nanolayer with mobility edge quantization for multi-value logic transistors. Nature Communications, 2019, 10, 1998.	5.8	67
23	Van der Waals junction field effect transistors with both n- and p-channel transition metal dichalcogenides. Npj 2D Materials and Applications, 2018, 2, .	3.9	66
24	Effects of substrate temperature on the device properties of pentacene-based thin film transistors using Al ₂ O _{3+x} gate dielectric. Journal of Applied Physics, 2004, 95, 3733-3736.	1.1	63
25	2D WSe ₂ /MoS ₂ van der Waals heterojunction photodiode for visible-near infrared broadband detection. Applied Physics Letters, 2018, 113, .	1.5	60
26	Spectral responsivity and quantum efficiency of n-ZnO/p-Si photodiode fully isolated by ion-beam treatment. Applied Physics Letters, 2003, 82, 3973-3975.	1.5	59
27	Non-Lithographic Fabrication of All-2D MoTe ₂ Dual Gate Transistors. Advanced Functional Materials, 2016, 26, 3146-3153.	7.8	55
28	Fabrication of p-pentacene/n-Si organic photodiodes and characterization of their photoelectric properties. Applied Physics Letters, 2003, 82, 639-641.	1.5	54
29	Direct imprinting of MoS ₂ flakes on a patterned gate for nanosheet transistors. Journal of Materials Chemistry C, 2013, 1, 7803.	2.7	50
30	Layer dependence and gas molecule absorption property in MoS ₂ Schottky diode with asymmetric metal contacts. Scientific Reports, 2015, 5, 10440.	1.6	49
31	Nonvolatile Charge Injection Memory Based on Black Phosphorous 2D Nanosheets for Charge Trapping and Active Channel Layers. Advanced Functional Materials, 2016, 26, 5701-5707.	7.8	49
32	Self-Powered Visible-Invisible Multiband Detection and Imaging Achieved Using High-Performance 2D MoTe ₂ /MoS ₂ Semivertical Heterojunction Photodiodes. ACS Applied Materials & Interfaces, 2020, 12, 10858-10866.	4.0	49
33	High-Responsivity Multilayer MoSe ₂ Phototransistors with Fast Response Time. Scientific Reports, 2018, 8, 11545.	1.6	48
34	Near-Infrared Self-Powered Linearly Polarized Photodetection and Digital Incoherent Holography Using WSe ₂ /ReSe ₂ van der Waals Heterostructure. ACS Nano, 2021, 15, 17917-17925.	7.3	46
35	Transition metal dichalcogenide heterojunction PN diode toward ultimate photovoltaic benefits. 2D Materials, 2016, 3, 045011.	2.0	45
36	Highly Sensitive Non-Classical Strain Gauge Using Organic Heptazole Thin-Film Transistor Circuit on a Flexible Substrate. Advanced Functional Materials, 2014, 24, 4413-4419.	7.8	44

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37	High-Gain Subnanowatt Power Consumption Hybrid Complementary Logic Inverter with WSe ₂ Nanosheet and ZnO Nanowire Transistors on Glass. <i>Advanced Materials</i> , 2015, 27, 150-156.	11.1	43
38	High-Performance 2D MoS ₂ Phototransistor for Photo Logic Gate and Image Sensor. <i>ACS Photonics</i> , 2018, 5, 4745-4750.	3.2	43
39	Monolayer MoS ₂ field-effect transistors patterned by photolithography for active matrix pixels in organic light-emitting diodes. <i>Npj 2D Materials and Applications</i> , 2019, 3, .	3.9	43
40	Transparent Photo-Stable Complementary Inverter with an Organic/Inorganic Nanohybrid Dielectric Layer. <i>Advanced Functional Materials</i> , 2009, 19, 726-732.	7.8	41
41	Ultrafast 27%GHz cutoff frequency in vertical WSe ₂ Schottky diodes with extremely low contact resistance. <i>Nature Communications</i> , 2020, 11, 1574.	5.8	39
42	Photo-Stable Organic Thin-Film Transistor Utilizing a New Indolocarbazole Derivative for Image Pixel and Logic Applications. <i>Advanced Functional Materials</i> , 2014, 24, 1109-1116.	7.8	38
43	Nonvolatile and Neuromorphic Memory Devices Using Interfacial Traps in Two-Dimensional WSe ₂ /MoTe ₂ Stack Channel. <i>ACS Nano</i> , 2020, 14, 12064-12071.	7.3	38
44	High-k and low-k nanocomposite gate dielectrics for low voltage organic thin film transistors. <i>Applied Physics Letters</i> , 2006, 88, 243515.	1.5	37
45	Hole transport in amorphous-crystalline-mixed and amorphous pentacene thin-film transistors. <i>Applied Physics Letters</i> , 2002, 81, 4640-4642.	1.5	35
46	ZnO-based thin-film transistors of optimal device performance. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004, 22, 1191.	1.6	34
47	42.3: Transparent ZnO Thin Film Transistor for the Application of High Aperture Ratio Bottom Emission AMOLED Display. <i>Digest of Technical Papers SID International Symposium</i> , 2008, 39, 629-632.	0.1	34
48	Work Function Tuning in Two-Dimensional MoS ₂ Field-Effect-Transistors with Graphene and Titanium Source-Drain Contacts. <i>Scientific Reports</i> , 2017, 7, 45546.	1.6	33
49	Enhancing the retention properties of ZnO memory transistor by modifying the channel/ferroelectric polymer interface. <i>Applied Physics Letters</i> , 2009, 95, 153502.	1.5	32
50	n-ZnO:N/p-Si nanowire photodiode prepared by atomic layer deposition. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	32
51	Coupling Two-Dimensional MoTe ₂ and InGaZnO Thin-Film Materials for Hybrid PN Junction and CMOS Inverters. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 15592-15598.	4.0	32
52	Transparent photostable ZnO nonvolatile memory transistor with ferroelectric polymer and sputter-deposited oxide gate. <i>Applied Physics Letters</i> , 2009, 95, 223506.	1.5	31
53	Origin of Bias-Stress Induced Instability in Organic Thin-Film Transistors with Semiconducting Small-Molecule/Insulating Polymer Blend Channel. <i>ACS Applied Materials & Interfaces</i> , 2013, 5, 1625-1629.	4.0	31
54	Transition Metal Dichalcogenide-Based Transistor Circuits for Gray Scale Organic Light-Emitting Displays. <i>Advanced Functional Materials</i> , 2017, 27, 1603682.	7.8	31

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55	The influence of sputtering power and O ₂ /Ar flow ratio on the performance and stability of Hf-In-Zn-O thin film transistors under illumination. Applied Physics Letters, 2010, 97, 102103.	1.5	30
56	Density of trap states measured by photon probe into ZnO based thin-film transistors. Applied Physics Letters, 2010, 97, .	1.5	30
57	2D MoSe ₂ Transistor with Polymer-Brush/Channel Interface. Advanced Materials Interfaces, 2018, 5, 1800812.	1.9	30
58	Enhanced Non-enzymatic amperometric sensing of glucose using Co(OH) ₂ nanorods deposited on a three dimensional graphene network as an electrode material. Mikrochimica Acta, 2016, 183, 2473-2479.	2.5	29
59	Few-Layer MoS ₂ -Organic Thin-Film Hybrid Complementary Inverter Pixel Fabricated on a Glass Substrate. Small, 2015, 11, 2132-2138.	5.2	28
60	Ambipolar Channel p-TMD/n-Ga ₂ O ₃ Junction Field Effect Transistors and High Speed Photo-sensing in TMD Channel. Advanced Materials, 2021, 33, e2103079.	11.1	28
61	Dual Gate ZnO-Based Thin-Film Transistors Operating at 5 V: nor Gate Application. IEEE Electron Device Letters, 2009, 30, 30-32.	2.2	26
62	Top and back gate molybdenum disulfide transistors coupled for logic and photo-inverter operation. Journal of Materials Chemistry C, 2014, 2, 8023-8028.	2.7	26
63	Large scale MoS ₂ nanosheet logic circuits integrated by photolithography on glass. 2D Materials, 2016, 3, 044001.	2.0	26
64	Impact of Organic Molecule-Induced Charge Transfer on Operating Voltage Control of Both n-MoS ₂ and p-MoTe ₂ Transistors. Nano Letters, 2019, 19, 2456-2463.	4.5	26
65	Intrinsic Correlation between Electronic Structure and Degradation: From Few-Layer to Bulk Black Phosphorus. Angewandte Chemie - International Edition, 2019, 58, 3754-3758.	7.2	26
66	Zero-Dimensional PbS Quantum Dot-InGaZnO Film Heterostructure for Short-Wave Infrared Flat-Panel Imager. ACS Photonics, 2020, 7, 1932-1941.	3.2	26
67	High-performance a MoS ₂ nanosheet-based nonvolatile memory transistor with a ferroelectric polymer and graphene source-drain electrode. Journal of the Korean Physical Society, 2015, 67, 1499-1503.	0.3	25
68	Charge-Transfer-Induced p-Type Channel in MoS ₂ Flake Field Effect Transistors. ACS Applied Materials & Interfaces, 2018, 10, 4206-4212.	4.0	25
69	Fully Transparent p-MoTe ₂ 2D Transistors Using Ultrathin MoO _x /Pt Contact Media for Indium-Oxide Source/Drain. Advanced Functional Materials, 2018, 28, 1801204.	7.8	25
70	Few-layered 1±-MoTe ₂ Schottky junction for a high sensitivity chemical-vapour sensor. Journal of Materials Chemistry C, 2018, 6, 10714-10722.	2.7	25
71	2D TMD Channel Transistors with ZnO Nanowire Gate for Extended Nonvolatile Memory Applications. Advanced Functional Materials, 2020, 30, 2004140.	7.8	24
72	Engineering MoSe ₂ /MoS ₂ heterojunction traps in 2D transistors for multilevel memory, multiscale display, and synaptic functions. Npj 2D Materials and Applications, 2022, 6, .	3.9	23

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73	The effect of localized surface plasmon on the photocurrent of silicon nanocrystal photodetectors. Applied Physics Letters, 2009, 94, 183108.	1.5	22
74	MoS ₂ nanosheet channel and guanine DNA-base charge injection layer for high performance memory transistors. Journal of Materials Chemistry C, 2014, 2, 5411-5416.	2.7	22
75	All-2D ReS ₂ transistors with split gates for logic circuitry. Scientific Reports, 2019, 9, 10354.	1.6	22
76	High Performance $\text{In}^2\text{Ga}_2\text{O}_3$ Schottky Barrier Transistors with Large Work Function TMD Gate of NbS ₂ and TaS ₂ . Advanced Functional Materials, 2021, 31, 2010303.	7.8	22
77	Channel/ferroelectric interface modification in ZnO non-volatile memory TFT with P(VDF-TrFE) polymer. Journal of Materials Chemistry, 2010, 20, 2638-2643.	6.7	21
78	Molybdenum Disulfide Nanoflake/Zinc Oxide Nanowire Hybrid Photoinverter. ACS Nano, 2014, 8, 5174-5181.	7.3	21
79	Electrical properties of aluminum oxide films deposited on indium-tin-oxide glasses. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 953.	1.6	20
80	DC Versus Pulse-Type Negative Bias Stress Effects on the Instability of Amorphous InGaZnO Transistors Under Light Illumination. IEEE Electron Device Letters, 2011, 32, 1704-1706.	2.2	20
81	Seamless MoTe ₂ Homojunction PIN Diode toward 1300 nm Short-Wave Infrared Detection. Advanced Optical Materials, 2019, 7, 1900768.	3.6	20
82	ZnO nanowire and mesowire for logic inverter fabrication. Applied Physics Letters, 2010, 97, 123506.	1.5	19
83	Nitrogen-doped ZnO/n-Si core-shell nanowire photodiode prepared by atomic layer deposition. Materials Science in Semiconductor Processing, 2015, 33, 154-160.	1.9	19
84	Analysis of Self-Heating Effect on Short Channel Amorphous InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2015, 36, 472-474.	2.2	19
85	Wafer-scale single-domain-like graphene by defect-selective atomic layer deposition of hexagonal ZnO. Nanoscale, 2015, 7, 17702-17709.	2.8	19
86	Integrated advantages from perovskite photovoltaic cell and 2D MoTe ₂ transistor towards self-power energy harvesting and photosensing. Nano Energy, 2019, 63, 103833.	8.2	19
87	Dynamic Oscillation via Negative Differential Resistance in Type III Junction Organic/2D-Dimensional and Oxide/2D-Dimensional Transition Metal Dichalcogenide Diodes. Advanced Functional Materials, 2021, 31, 2009436.	7.8	19
88	Determining the optimum pentacene channel thickness on hydrophobic and hydrophilic dielectric surface. Applied Physics Letters, 2008, 93, .	1.5	18
89	ZnO-based low voltage inverter with low-k/high-k double polymer dielectric layer. Applied Physics Letters, 2008, 93, 193514.	1.5	18
90	The Influence of In/Zn Ratio on the Performance and Negative-Bias Instability of Hf/In/ZnO Thin-Film Transistors Under Illumination. IEEE Electron Device Letters, 2011, 32, 1251-1253.	2.2	18

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91	Dramatic Reduction of Contact Resistance via Ultrathin LiF in Two-Dimensional MoS ₂ Field Effect Transistors. Nano Letters, 2021, 21, 3503-3510.	4.5	18
92	Direct Thermal Growth of Large Scale Cl-doped CdTe Film for Low Voltage High Resolution X-ray Image Sensor. Scientific Reports, 2018, 8, 14810.	1.6	16
93	Low Voltage and Ferroelectric 2D Electron Devices Using Lead-free Ba x Sr 1-x TiO 3 and MoS 2 Channel. Advanced Functional Materials, 2020, 30, 1908210.	7.8	16
94	Photoexcited charge collection spectroscopy of two-dimensional polaronic states in polymer thin-film transistors. Physical Review B, 2012, 85, .	1.1	15
95	Capacitance-Voltage Measurement With Photon Probe to Quantify the Trap Density of States in Amorphous Thin-Film Transistors. IEEE Electron Device Letters, 2012, 33, 1015-1017.	2.2	15
96	NiOx Schottky-gated ZnO nanowire metal-semiconductor field effect transistor: fast logic inverter and photo-detector. Journal of Materials Chemistry C, 2014, 2, 4428.	2.7	15
97	Hydrogen Barriers Based on Chemical Trapping Using Chemically Modulated Al ₂ O ₃ Grown by Atomic Layer Deposition for InGaZnO Thin-Film Transistors. ACS Applied Materials & Interfaces, 2021, 13, 20349-20360.	4.0	15
98	Passivation effects on the stability of pentacene thin-film transistors with SnO ₂ prepared by ion-beam-assisted deposition. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 2357.	1.6	14
99	Quaternary NAND Logic and Complementary Ternary Inverter with p-MoS ₂ /n-MoS ₂ Heterostack Channel Transistors. Advanced Functional Materials, 2022, 32, .	7.8	14
100	ZnO nanowire transistor inverter using top-gate electrodes with different work functions. Applied Physics Letters, 2011, 99, 153507.	1.5	13
101	Charge Transport in 2D DNA Tunnel Junction Diodes. Small, 2017, 13, 1703006.	5.2	13
102	Quantitative photon-probe evaluation of trap-containing channel/dielectric interface in organic field effect transistors. Journal of Materials Chemistry, 2010, 20, 2659.	6.7	12
103	Organic-inorganic nanohybrid nonvolatile memory transistors for flexible electronics. Journal of Materials Chemistry, 2012, 22, 19007.	6.7	12
104	Stability, efficiency, and mechanism of n-type doping by hydrogen adatoms in two-dimensional transition metal dichalcogenides. Physical Review B, 2019, 100, .	1.1	12
105	Advanced Multifunctional Field Effect Devices Using Common Gate for Both 2D Transition-Metal Dichalcogenide and InGaZnO Channels. Advanced Electronic Materials, 2019, 5, 1900730.	2.6	12
106	Complementary Type Ferroelectric Memory Transistor Circuits with p- and n-Channel MoTe ₂ . Advanced Electronic Materials, 2020, 6, 2000479.	2.6	12
107	Nanowatt use 8ÅV switching nonvolatile memory transistors with 2D MoTe ₂ channel and ferroelectric P(VDF-TrFE). Nano Energy, 2021, 81, 105686.	8.2	12
108	Columnar deformation of human red blood cell by highly localized fiber optic Bessel beam stretcher. Biomedical Optics Express, 2015, 6, 4417.	1.5	11

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109	Impact of H ⁺ Doping on n ⁺ Type TMD Channels for Low-Temperature Band-Like Transport. <i>Small</i> , 2019, 15, e1901793.	5.2	11
110	Annealing-induced conductivity transition in ZnO nanowires for field-effect devices. <i>Applied Physics Letters</i> , 2012, 101, 043504.	1.5	10
111	Polymer/oxide bilayer dielectric for hysteresis-minimized 1ÅV operating 2D TMD transistors. <i>RSC Advances</i> , 2018, 8, 2837-2843.	1.7	10
112	Ferroelastic-Ferroelectric Multiferroicity in van der Waals Rhenium Dichalcogenides. <i>Advanced Materials</i> , 2022, 34, e2108777.	11.1	10
113	Infrared spectroscopy of the interface charge in a ZnO field-effect transistor. <i>Applied Physics Letters</i> , 2008, 93, 241902.	1.5	8
114	NOT and NOR Logic Circuits Using Passivation Dielectric Involved Dual Gate in a-InGaZnO TFTs. <i>IEEE Electron Device Letters</i> , 2013, 34, 1527-1529.	2.2	8
115	Interband Transitions in Monolayer and Few-Layer WSe ₂ Probed Using Photoexcited Charge Collection Spectroscopy. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 20213-20218.	4.0	8
116	2D MoS ₂ Charge Injection Memory Transistors Utilizing Hetero-Stack SiO ₂ /HfO ₂ Dielectrics and Oxide Interface Traps. <i>Advanced Electronic Materials</i> , 2021, 7, 2100074.	2.6	8
117	Single-Crystalline Silicon-Based Heterojunction Photodiode Arrays on Flexible Plastic Substrates. <i>IEEE Transactions on Electron Devices</i> , 2011, 58, 3329-3334.	1.6	7
118	Deep blue energy harvest photovoltaic switching by heptazole-based organic Schottky diode circuits. <i>NPG Asia Materials</i> , 2016, 8, e278-e278.	3.8	7
119	Tungsten Dichalcogenide Nanoflake/InGaZnO Thin-Film Heterojunction for Photodetector, Inverter, and AC Rectifier Circuits. <i>Advanced Electronic Materials</i> , 2020, 6, 2000026.	2.6	7
120	Ambient-protecting organic light transducer grown on pentacene-channel of photo-gating complementary inverter. <i>Journal of Materials Chemistry</i> , 2012, 22, 4444.	6.7	6
121	Intrinsic Correlation between Electronic Structure and Degradation: From Few-Layer to Bulk Black Phosphorus. <i>Angewandte Chemie</i> , 2019, 131, 3794-3798.	1.6	6
122	High-Performance van der Waals Junction Field-Effect Transistors Utilizing Organic Molecule/Transition Metal Dichalcogenide Interface. <i>ACS Nano</i> , 2020, 14, 15646-15653.	7.3	6
123	Single-Crystalline Metallic Films Induced by van der Waals Epitaxy on Black Phosphorus. <i>Chemistry of Materials</i> , 2021, 33, 3593-3601.	3.2	6
124	Photogating and electrical-gating of amorphous GaSnZnO-based inverter with light-transmitting gate electrode. <i>Applied Physics Letters</i> , 2011, 98, 223505.	1.5	5
125	Transparent p ⁺ NiO/n ⁺ ZnO diodes used in circuit rectifiers. <i>Physica Status Solidi - Rapid Research Letters</i> , 2012, 6, 475-477.	1.2	5
126	Low-voltage pentacene transistor inverters using micro-contact printed nano-layer. <i>Journal of Materials Chemistry</i> , 2010, 20, 663-665.	6.7	4

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127	Sputter-deposited Ga-Sn-Zn-O thin films for transparent thin film transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011, 208, 2934-2938.	0.8	4
128	The effects of surface modification on the electrical properties of n + junction silicon nanowires grown by an aqueous electroless etching method. <i>Journal of Nanoparticle Research</i> , 2012, 14, 1.	0.8	4
129	Manipulating ZnO nanowires for field-effect device integration by optical-fiber grip coated with thermoplastic copolymer. <i>Journal of Materials Chemistry C</i> , 2013, 1, 7303.	2.7	4
130	Threshold voltage control by gate electrode in Ga-Sn-Zn-O thin-film transistors for logic inverter application. <i>Physica Status Solidi - Rapid Research Letters</i> , 2011, 5, 211-213.	1.2	3
131	Instability of amorphous hafnium-indium-zinc-oxide thin film transistors under negative-bias-illumination stress. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	3
132	Innenr¼cktitelbild: Intrinsic Correlation between Electronic Structure and Degradation: From Few-layer to Bulk Black Phosphorus (<i>Angew. Chem.</i> 12/2019). <i>Angewandte Chemie</i> , 2019, 131, 4107-4107.	1.6	3
133	Density-Dependent Microstructures and Electromechanical Properties of Amorphous InGaZnO ₄ Semiconductors: An Ab Initio Study. <i>ACS Applied Electronic Materials</i> , 2022, 4, 2545-2551.	2.0	3
134	Ferroelectric property improvement of poly(vinylidene fluoride/trifluoroethylene) polymer exposed to a plasma ambient. <i>Applied Physics Letters</i> , 2010, 97, 162911.	1.5	2
135	Room Temperature Cmcm Phase of CaxSn1-xSe for Thermoelectric Energy Conversion. <i>ACS Applied Energy Materials</i> , 0, , .	2.5	2
136	Damage-free Charge Transfer Doping of 2D Transition Metal Dichalcogenide Channels by van der Waals Stamping of MoO ₃ and LiF. <i>Small Methods</i> , 2022, , 2101073.	4.6	2
137	Nonvolatile memory properties in ZnO-based thin-film transistors with polymer ferroelectric and thin buffer layer. , 2010, , .		1
138	ZnO nanowire manipulation and transportation using thermoplastic and tapered silica nanowire. , 2012, , .		1
139	All-fiber 1-D optical stretcher for bio-cells implemented in a Lab-on-a-Chip. , 2013, , .		1
140	Origin of channel/dielectric interfacial trap states modification by ultraviolet irradiation on organic thin-film transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 2886-2889.	0.8	1
141	Reliable semi-transparent pentacene thin-film transistors with polymer gate dielectric layers cured at an optimum temperature. <i>Materials Research Society Symposia Proceedings</i> , 2005, 905, 1.	0.1	0
142	Terahertz time-domain spectroscopy of NiO _x thin films. , 2009, , .		0
143	Thin-Film Transistors: Transparent Photo-Stable Complementary Inverter with an Organic/Inorganic Nanohybrid Dielectric Layer (<i>Adv. Funct. Mater.</i> 5/2009). <i>Advanced Functional Materials</i> , 2009, 19, NA-NA.	7.8	0
144	Self-assembled organic channel-polymer dielectric layer for organic thin-film transistor applications. <i>AIP Conference Proceedings</i> , 2011, , .	0.3	0

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145	Data Storage: MoS ₂ Nanosheets for Top-Gate Nonvolatile Memory Transistor Channel (Small 20/2012). Small, 2012, 8, 3220-3220.	5.2	0
146	3-D Manipulation of ZnO Nanowire Using Optically Activated Thermoplastic Tip on Silica Fiber Taper. IEEE Photonics Technology Letters, 2014, 26, 2001-2003.	1.3	0
147	Organic Field-Effect Transistors: Critical Factors to Achieve Low Voltage- and Capacitance-Based Organic Field-Effect Transistors (Adv. Mater. 2/2014). Advanced Materials, 2014, 26, 194-194.	11.1	0
148	Comparative studies on ZnO thin-film transistors with inorganic versus polymer dielectric interfaces. Journal of the Korean Physical Society, 2015, 67, 537-540.	0.3	0
149	Reply to "Comment on "Metal Semiconductor Field-Effect Transistor with MoS ₂ /Conducting NiO _x van der Waals Schottky Interface for Intrinsic High Mobility and Photoswitching Speed" ACS Nano, 2016, 10, 1716-1717.	7.3	0